

XP-002278440

1/6 - (C) FILE CA

STN CA Caesar accession number : 1502

AN - 132:229833 CA

TI - Method and apparatus for CVD of silicon nitride, and apparatus for removing ammonium halide

IN - Sato, Yusuke; Kataoka, Takashi; Tamaoki, Naoki; Ohmine, Toshimitsu

PA - Toshiba Corp., Japan

SO - Jpn. Kokai Tokkyo Koho, 11 pp.

CODEN: JKXXAF

DT - Patent

LA - Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PN	JP2000080476	A2	20000321	JP 1999-179218	19990625
	US2001048973	A1	20011206	US 1999-344484	19990625
	US6365231	B2	20020402		
PRAI-	JP 1998-180436	A	19980626		

OS - MARPAT 132:229833

AB - A method for CVD of a silicon nitride film involves using $\text{SiH}_4\text{-x(NH}_2\text{)}_x$ ($x.\text{gtoreq.}2$), or SiH_2NH , or Si(NH)_2 , or $(\text{SiH}_2\text{NH})_x$, or $\text{NH}_2(\text{SiH}_2\text{NH})_x\text{SiH}_2\text{NH}_2$ ($x>1$), or $\text{SiH}_4\text{-x(NHR)}_x$ ($x.\text{gtoreq.}2$, $\text{R}=\text{H, F, F-substitutable C1-3 hydrocarbon group}$), or $\text{SiH}_4\text{-x-y(NH}_2\text{)}_x(\text{NHR})_y$ ($x+y.\text{ltoreq.}4$, $x,y.\text{gtoreq.}1$), or SixNyHz ($y.\text{gtoreq.}2$), or SixNyHzFu . Addnl., NH_3 , hydrazine (or its deriv.), or HCl may be used. An app. for carrying out the above method is also described. An app. for removing an ammonium halide from the above app. is also described. The method and app. are useful for semiconductor device fabrication.

IT - 208238-68-0

RL: NUU (Other use, unclassified); USES (Uses)

(method and app. for CVD of silicon nitride, and app. for removing ammonium halide)

RN - 208238-68-0 CA

CN Hydrazine, 1-methyl-1-silyl- (9CI) (CA INDEX NAME)

